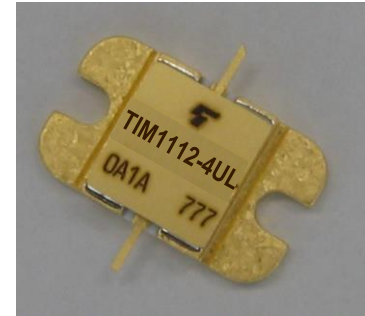


FEATURES

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER
P1dB= 36.5dBm at 11.7GHz to 12.7GHz
- HIGH GAIN
G1dB= 9.5dB at 11.7GHz to 12.7GHz
- LOW INTERMODULATION DISTORTION
IM3=-45dBc at Pout= 24.0dBm
Single Carrier Level
- HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 1.0A f=11.7 to 12.7 GHz	dBm	35.5	36.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.5	9.5	—
Drain Current	IDS1		A	—	1.1	1.6
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	36	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 24.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	1.1	1.6
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C	—	—	60

Recommended Gate Resistance(Rg): 150 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

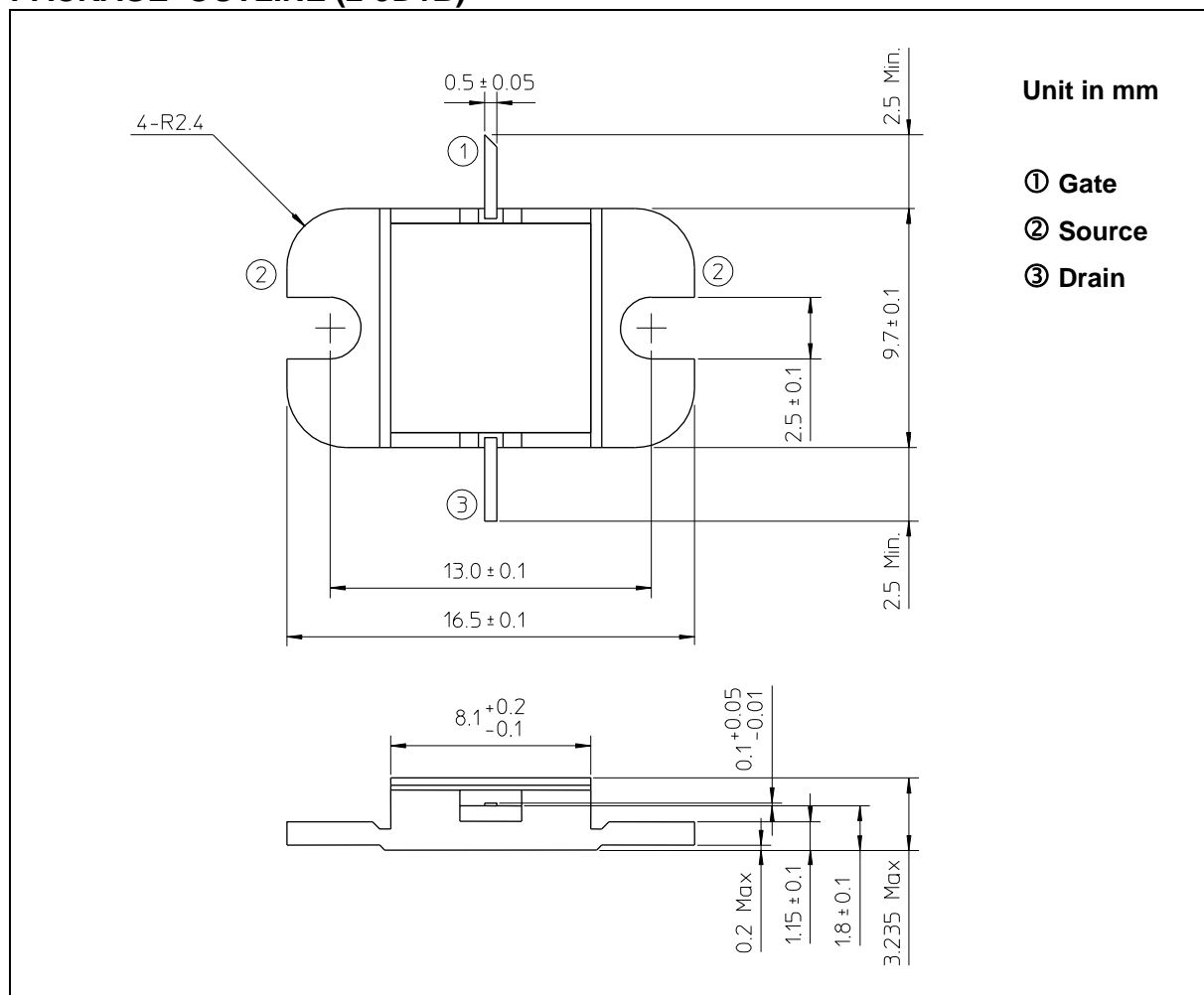
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 1.2A	S	—	1.2	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-0.5	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	2.2	—
Gate-Source Breakdown Voltage	VGSO	IGS= -40μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	3.8	4.4

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	3.3
Total Power Dissipation (Tc= 25°C)	PT	W	34.1
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.